

***Supporting Information***

**Tuning the Seebeck Effect in C60-based Hybrid Thermoelectric Devices through  
Temperature-dependent Surface Polarization and Thermally-modulated Interface  
Dipoles**

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## 1. The XRD patterns of the oxide film on ITO glass

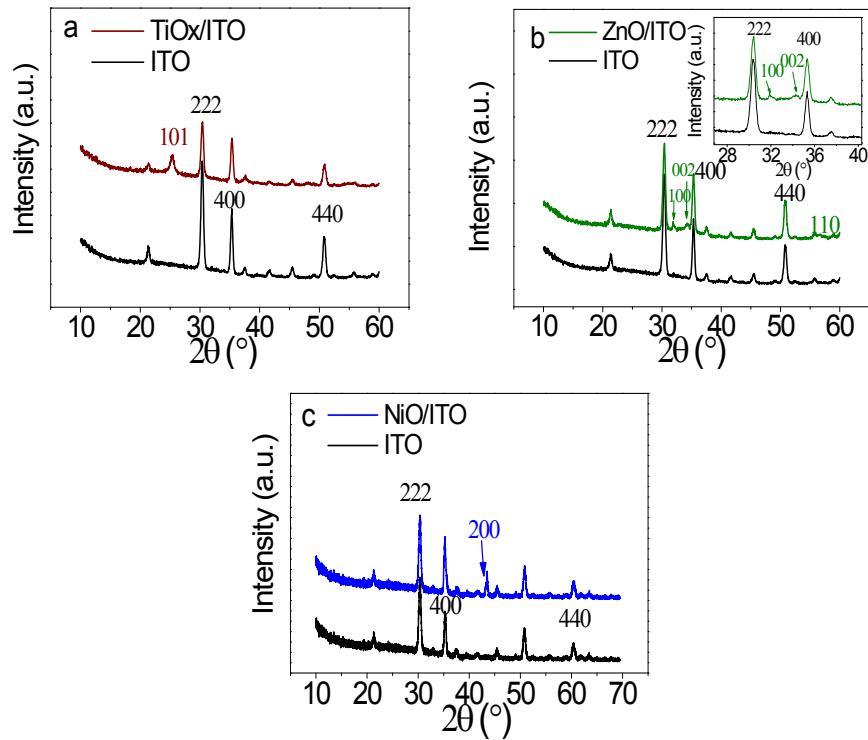


Figure S1: the XRD patterns of the oxide film prepared from the solution method: (a)  $\text{TiO}_x$ , (b)  $\text{ZnO}$ , (c)  $\text{NiO}$ . The black line is the XRD for ITO glass substrate.

## 2. The work function of the oxide film measured by Kelvin Probe

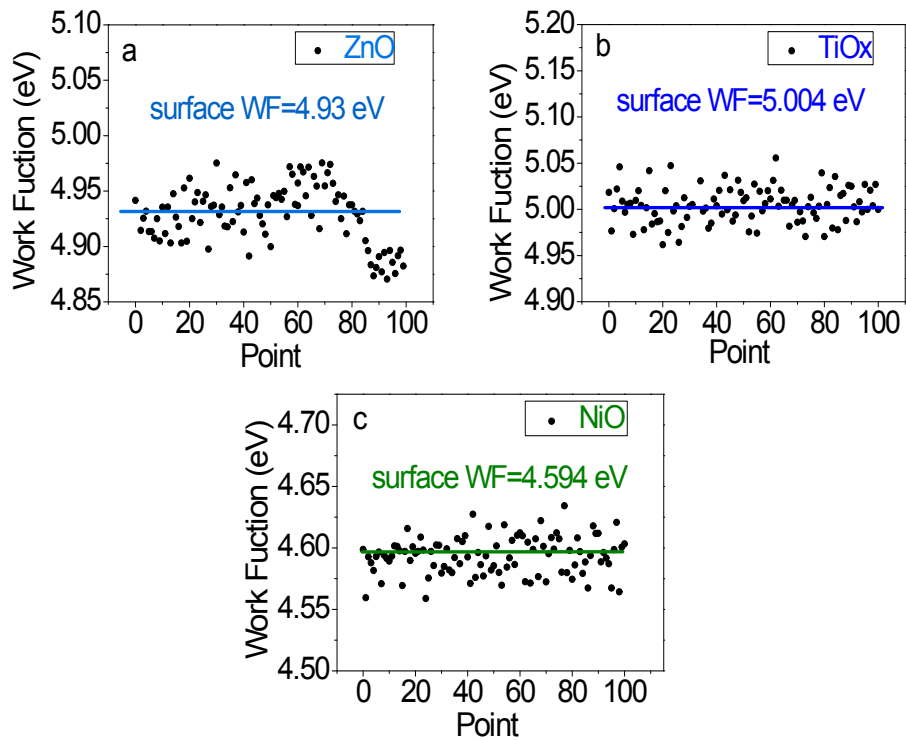


Figure S2: the work function (a)  $\text{TiO}_x$ , (b)  $\text{ZnO}$ , (c)  $\text{NiO}$ , measured from Kelvin Probe at room temperature:

### 3. The thermovoltage as a function of temperature difference in the thin-film devices

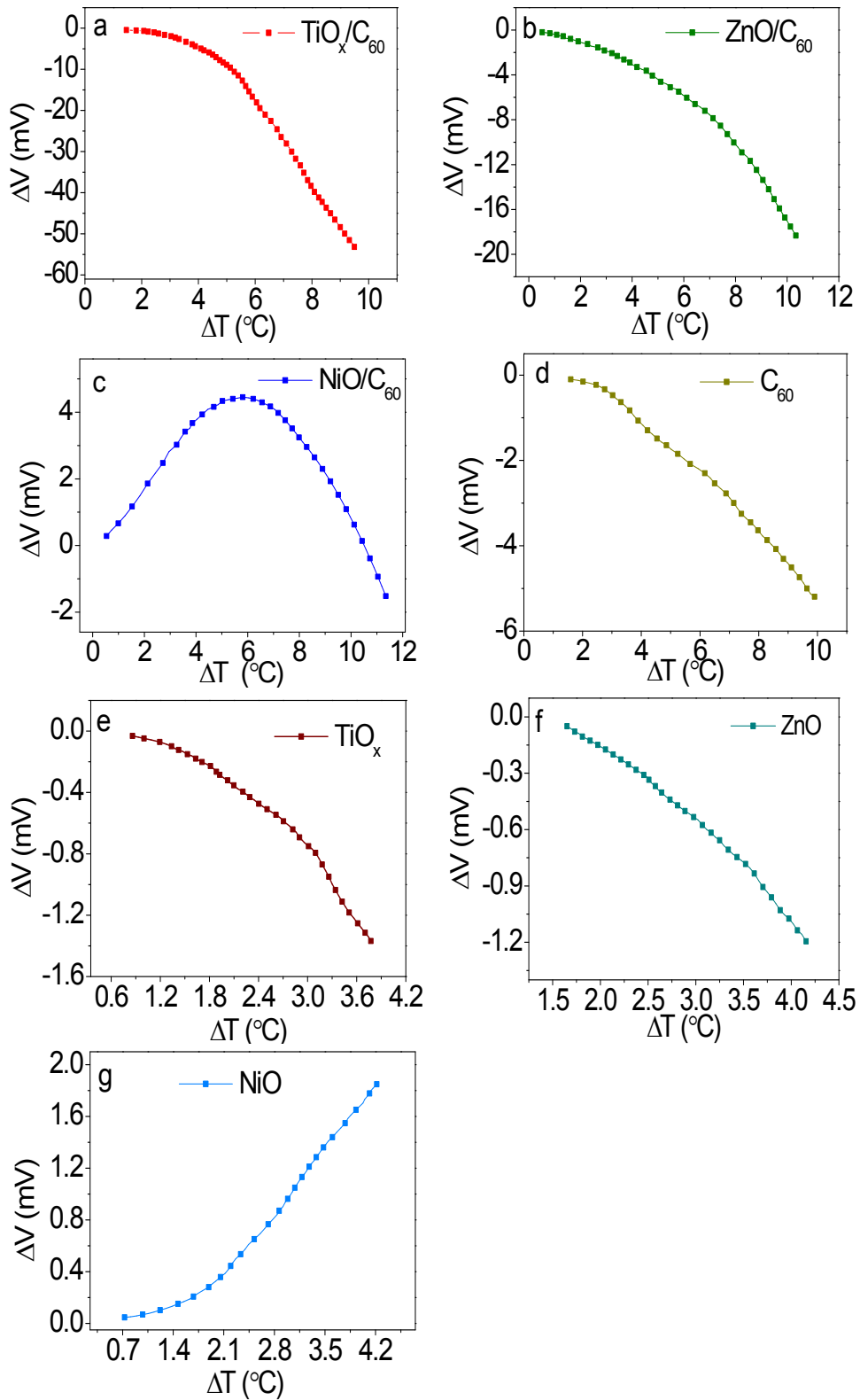


Figure S3: The thermovoltage as a function of temperature difference in the thin-film devices of (a) ITO/ $\text{TiO}_x/\text{C}_{60}/\text{Al}$ , (b) ITO/ $\text{ZnO}/\text{C}_{60}/\text{Al}$ , (c) ITO/ $\text{NiO}/\text{C}_{60}/\text{Al}$  (d) ITO/ $\text{C}_{60}/\text{Al}$ , (e) ITO/ $\text{TiO}_x/\text{Al}$ , (f) ITO/ $\text{ZnO}/\text{Al}$ , (g) ITO/ $\text{NiO}/\text{Al}$ .

#### 4. The temperature dependence of electrical conductivity in the single-layer devices

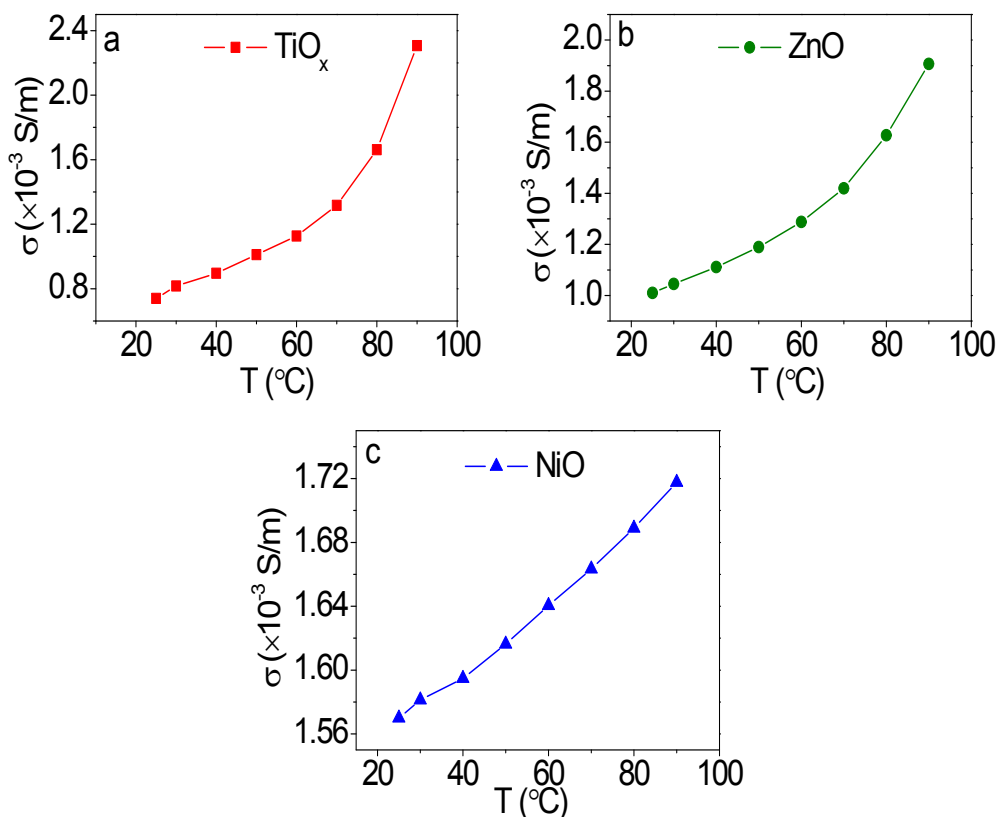


Figure S4: The temperature dependence of electrical conductivity in the single-layer devices: (a) ITO/ $\text{TiO}_x$ /Al, (b) ITO/ $\text{ZnO}$ /Al, (c) ITO/ $\text{NiO}$ /Al.

#### 5. The calculated power factor of $\text{C}_{60}$ devices

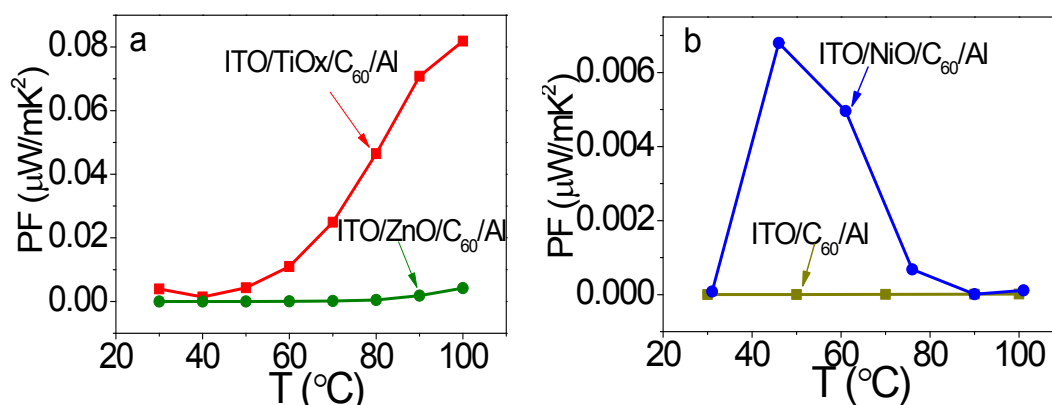


Figure S5: the calculated power factor of devices at different temperature: (a) ITO/ $\text{TiO}_x$ / $\text{C}_{60}$ /Al and ITO/ $\text{ZnO}$ / $\text{C}_{60}$ /Al, (b) ITO/ $\text{TiO}_x$ / $\text{C}_{60}$ /Al and ITO/ $\text{C}_{60}$ /Al.

<b>Table 1</b>			
<b>DEVICE</b>	$\frac{V_0}{V_T}$ (AT=30°C)	$\frac{V_0}{V_T}$ (AT=45°C)	$\frac{V_0}{V_T}$ (AT=60°C)
ITO/C <sub>60</sub> /Al	3.3%	3%	1.8%
Al/C <sub>60</sub> /Al	4.3%	3.5%	2.8%
ITO/ZnO/Al	2.5%	1.8%	1.7%
ITO/TiO <sub>x</sub> /Al	1.8%	1.6%	2.1%
ITO/NiO/Al	2.7%	2.5%	1.8%
ITO/ZnO/C <sub>60</sub> /Al	4.7%	3.4%	2.9%
ITO/TiO <sub>x</sub> /C <sub>60</sub> /Al	5.8%	4.8%	6.3%
ITO/NiO/C <sub>60</sub> /Al	3.7%	3.1%	4.9%

Table 1: The percentage of  $\frac{V_0}{V_T}$  for different devices at the average temperature of 30°C, 45°C, and 60°C, where the  $V_0$  and  $V_T$  are the measured voltage signals between the two electrodes of the devices measured without and with temperature difference, and AT is average temperature of the two electrodes.